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## **Supplementary information**

In order to understand the surface band states, we further calculated the banddecomposed charge density distributions at  $\overline{\Gamma}$  point near the Fermi level for Ca/Si(111)- $3 \times 2$  and Ba/Si(111)- $3 \times 2$  surfaces. As shown in Fig. S1(b) and S2(b), for each case the first conduction bands (CB<sub>1</sub>) have  $\pi^*$  antibonding character between  $p_z$  orbital of the surface Si(C) and Si(D) atoms. The corresponding charge distribution are mainly contributed by the surface Si(C) and Si(D) atoms, while the charge contributions of Si atoms in the second layer and metal atoms are small. Meanwhile, for the first and second valence bands ( $VB_1$  and  $VB_2$ ) we find that there are no charge contribution from Si atoms in the topmost layer and metal atom, and all charge distribution are contributed by the bulk Si atoms. Similar to  $CB_1$ , the third valance bands (VB<sub>3</sub>) are primarily contributed by the  $d_{xy}$  orbital of metal adatom and the  $p_x$  orbital of surface Si(A) and Si(B) atoms. These results clearly indicate that CB<sub>1</sub> and VB<sub>3</sub> are the surface states, while the  $VB_1$  and  $VB_2$  are not. Therefore, the surface band gap are between CB<sub>1</sub> and VB<sub>3</sub> bands, and the corresponding values are estimated to be 1.65 and 1.66 eV for Ca and Ba, respectively. These values are in good agreement with the experimental data of 1.7 eV for Sr/Si(111)-(3×2) surface. <sup>[1]</sup>



FIG. S1: (a) Calculated electronic band structure of Ca/Si(111)-3×2 surface using HSE06 functional. Horizonal dotted line gives the Fermi level that is set to zero. (b) The band-decomposed charge density distributions at  $\overline{\Gamma}$  point. VB<sub>1</sub>, VB<sub>2</sub> and VB<sub>3</sub> represent the first, second and third valence band, respectively, and CB<sub>1</sub> represent the first conduction band. The color spacing is 0.005 e/Å<sup>3</sup>. The Si atoms in the first layer



are plotted in red, the other Si atoms are in blue, and the AEM atoms are in grey.

FIG. S2: (a) Calculated electronic band structure of Ba/Si(111)-3×2 surface using HSE06 functional. Horizonal dotted line gives the Fermi level that is set to zero. (b) The band-decomposed charge density distributions at  $\overline{\Gamma}$  point. VB<sub>1</sub>, VB<sub>2</sub> and VB<sub>3</sub> represent the first, second and third valence band, respectively, and CB<sub>1</sub> represent the

first conduction band. The color spacing is 0.005 e/Å<sup>3</sup>. The Si atoms in the first layer are plotted in red, the other Si atoms are in blue, and the AEM atoms are in green. REFERENCES

[1] W. H. Du and J. J. Yang, Surf. Sci., 2016, 653, 222.